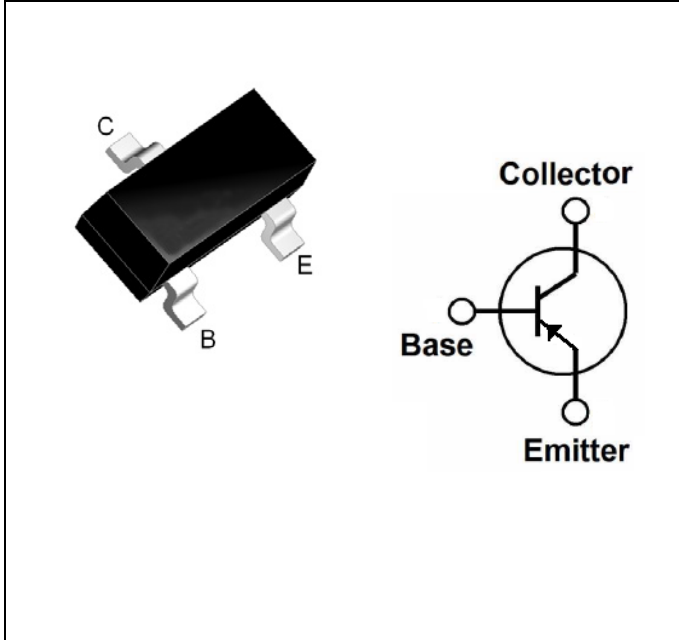


GENERAL PURPOSE TRANSISTORS PNP Silicon



FEATURES

- High DC Current Gain
- High Voltage and High Current
- Complementary to 2SC4116
- Small Package

MECHANICAL DATA

- Available in SOT-323 Package
- Solderability : MIL-STD-202, Method 208
- Full RoHS Compliance

PART NUMBER	PACKAGE	SHIPPING	MARKING
2SA1586□-△-3T3R	SOT-323	Tape Reel	See Classification Of hFE

Notes:

1. □: none is for Lead Free package;
"G" is for Halogen Free package.
2. △: Rank Of hFE; See Classification Of hFE
3. Marking Code: yww: y: Year code; ww: Week code.

THERMAL DATA

PARAMETER	SYMBOL	VALUES	UNIT
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	1250	°C/W

Notes:

4. The value of $R_{\theta JA}$ is measured with device mounted on 1 in² FR-4 board with 2 oz copper.

ABSOLUTE MAXIMUM RATINGS

$T_A = 25^\circ\text{C}$, unless otherwise noted.

PARAMETER	SYMBOL	VALUES	UNIT
Collector-Emitter Voltage	V_{CEO}	-50	V
Collector-Base Voltage	V_{CBO}	-50	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-150	mA
Power Dissipation @ $T_A = 25^\circ\text{C}$	P_C	100	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 ~ +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS

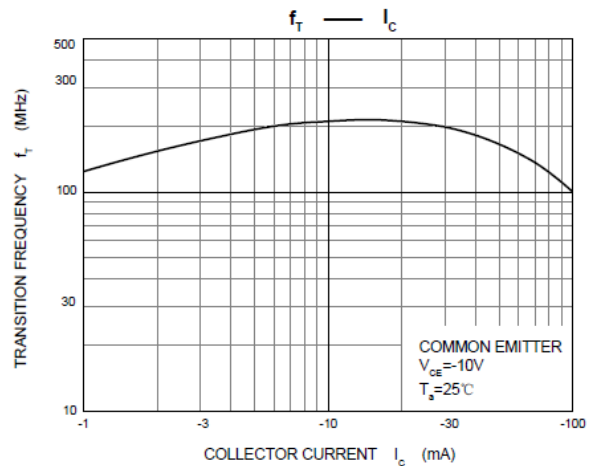
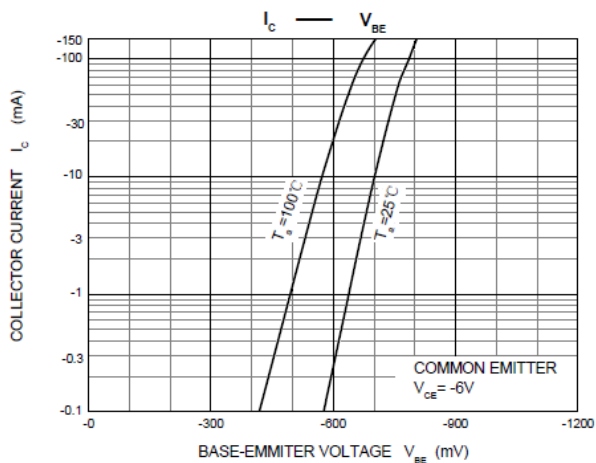
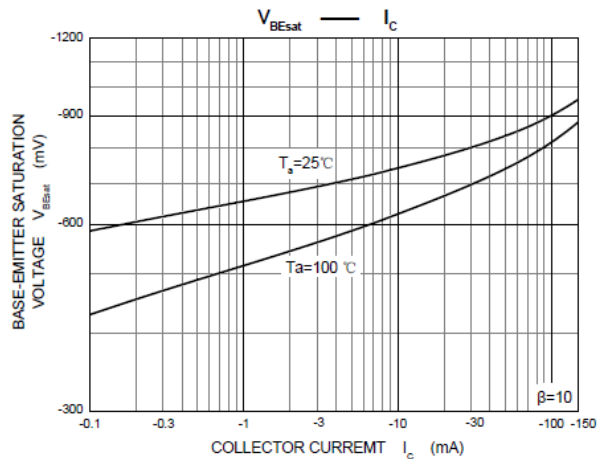
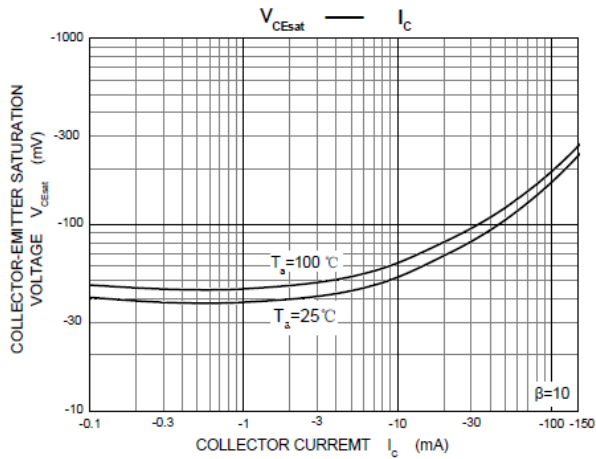
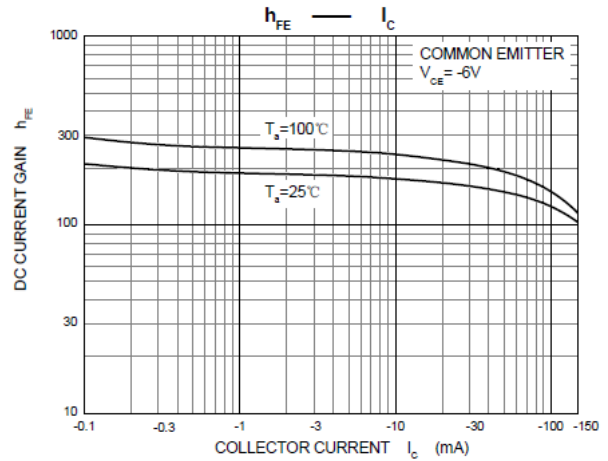
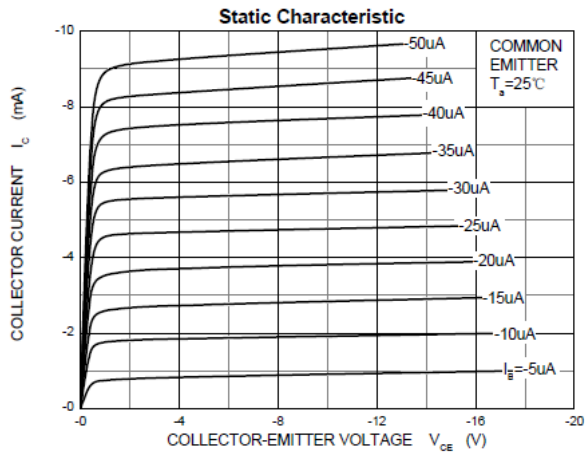
$T_A = 25^\circ\text{C}$, unless otherwise noted.

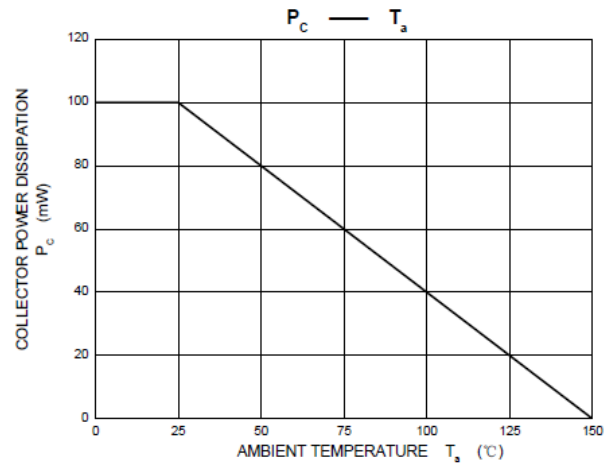
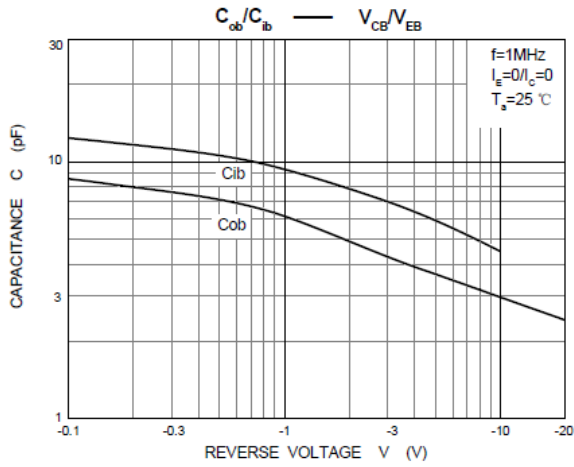
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B = 0$	-50			V
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -100\ \mu\text{A}, I_E = 0$	-50			V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -100\ \mu\text{A}, I_C = 0$	-5			V
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5\text{V}, I_C = 0$			-0.1	μA
Collector Cut-off Current	I_{CBO}	$V_{CB} = -50\text{V}, I_E = 0$			-0.1	μA
ON CHARACTERISTICS						
DC Current Gain	h_{FE}	$I_C = -2\text{mA}, V_{CE} = -6\text{V}$	70		400	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -100\text{mA}, I_B = -10\text{mA}$			-0.3	V
SMALL-SIGNAL CHARACTERISTICS						
Transition Frequency	f_T	$I_C = -1\text{mA}, V_{CE} = -10\text{V}$	80			MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$			7	pF

CLASSIFICATION OF h_{FE}

RANK	O	Y	GR
h_{FE} RANGE	70~140	120~240	200~400
MARKING	SO	SY	SG

TYPICAL PERFORMANCE CHARACTERISTICS





PHYSICAL DIMENSION

Unit : Inch (Millimeter)

